24. The method for classifying defects as described in claim 7 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

25. The method for classifying defects as described in claim 10 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

26. The method for classifying defects as described in claim 9 wherein said first category relates to defect type.

27. The method for classifying defects as described in claim 26 wherein said defect type includes particle defects, flaw defects, circuit pattern defects, and voltage contrast defects.

28. The method for classifying defects as described in claim 9 wherein said second category relates to defect criticality.

REMARKS

Claims 1-11 and 23-28 are pending. Claims 12-22 have been canceled without prejudice pursuant to the restriction requirement. New claims 23-28 have been added. No new matter has been introduced. Applicants believe the claims comply with 35 U.S.C. § 112.

CONCLUSION

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 650-326-2400.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please cancel claims 12-22 without prejudice and add the following new claims.

12.-22. CANCELED.

--23. The method for classifying defects as described in claim 2 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

24. The method for classifying defects as described in claim 7 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

25. The method for classifying defects as described in claim 10 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

26. The method for classifying defects as described in claim 9 wherein said first category relates to defect type.

27. The method for classifying defects as described in claim 26 wherein said defect type includes particle defects, flaw defects, circuit pattern defects, and voltage contrast defects.

28. The method for classifying defects as described in claim 9 wherein said second category relates to defect criticality.--